

HiPerFRED

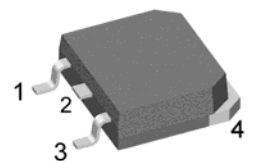
$$\begin{aligned} V_{RRM} &= 600 \text{ V} \\ I_{FAV} &= 60 \text{ A} \\ t_{rr} &= 35 \text{ ns} \end{aligned}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

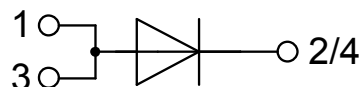
Part number

DSEP60-06AT

Marking on Product: DSEP60-06AT



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-268AA (D3Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

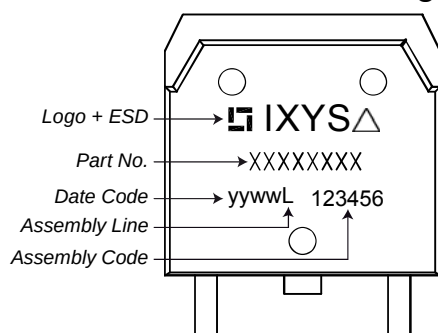
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			650	μA	
		V _R = 600 V	T _{VJ} = 150°C			2,5	mA	
V _F	forward voltage drop	I _F = 60 A	T _{VJ} = 25°C			2,04	V	
		I _F = 120 A				2,33	V	
		I _F = 60 A	T _{VJ} = 150°C			1,39	V	
		I _F = 120 A				1,70	V	
I _{FAV}	average forward current	T _C = 130°C rectangular d = 0.5	T _{VJ} = 175°C			60	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		0,95	V	
r _F	slope resistance					5	mΩ	
R _{thJC}	thermal resistance junction to case					0,45	K/W	
R _{thCH}	thermal resistance case to heatsink				0,15		K/W	
P _{tot}	total power dissipation	T _C = 25°C				330	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		600	A	
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C	67		pF	
I _{RM}	max. reverse recovery current	} I _F = 60 A; V _R = 300 V -di _F /dt = 200 A/μs		T _{VJ} = 25°C	8		A	
				T _{VJ} = 100°C	13		A	
t _{rr}	reverse recovery time			T _{VJ} = 25°C	35		ns	
				T _{VJ} = 100°C	110		ns	

Package TO-268AA (D3Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				5		g
F_c	mounting force with clip		20		120	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



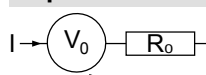
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP60-06AT-TUB	DSEP60-06AT	Tube	30	509748

Similar Part	Package	Voltage class
DSEP60-06A	TO-247AD (2)	600
DHG60I600HA	TO-247AD (2)	600
DPH30IS600HI	ISOPLUS247 (2)	600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Fast Diode

$V_{0 \max}$ threshold voltage

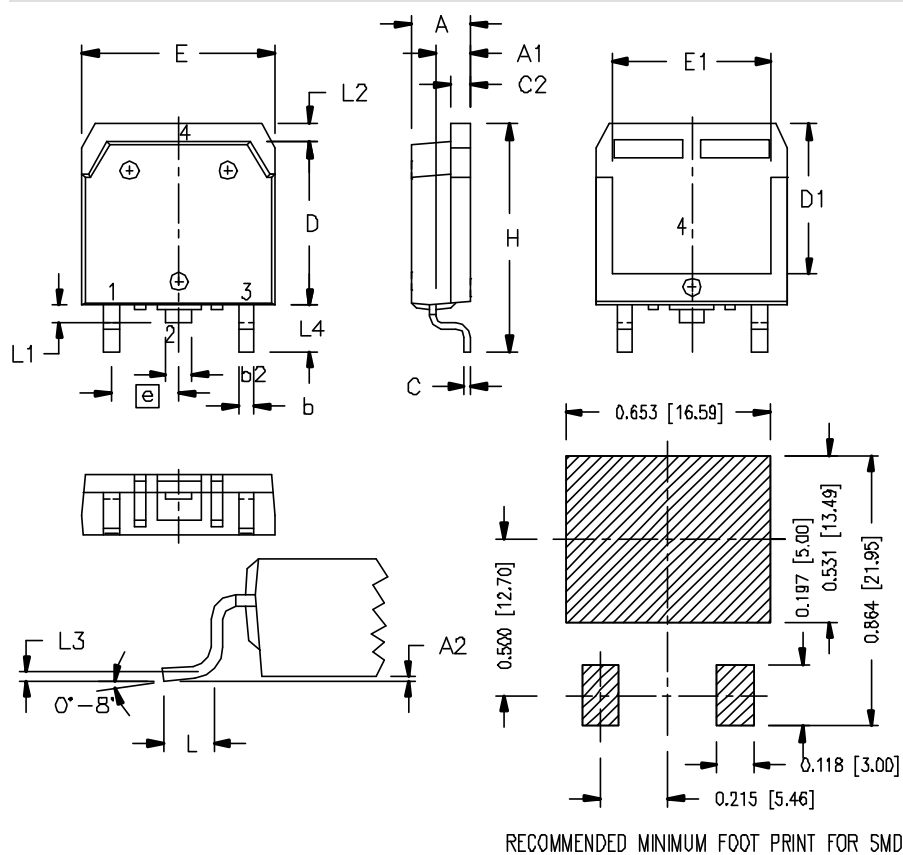
0,95

V

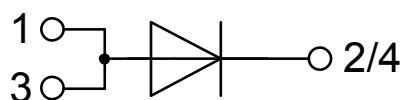
$R_{0 \max}$ slope resistance *

2,4

mΩ

Outlines TO-268AA (D3Pak)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.90	5.10	0.193	0.201
A1	2.70	2.90	0.106	0.114
A2	0.02	0.25	0.001	0.100
b	1.15	1.45	0.045	0.057
b2	1.90	2.10	0.075	0.083
C	0.40	0.65	0.016	0.026
C2	1.45	1.60	0.057	0.063
D	13.80	14.00	0.543	0.551
D1	12.40	12.70	0.488	0.500
E	15.85	16.05	0.624	0.632
E1	13.30	13.60	0.524	0.535
e	5.45 BSC		0.215 BSC	
H	18.70	19.10	0.736	0.752
L	2.40	2.70	0.094	0.106
L1	1.20	1.40	0.047	0.055
L2	1.00	1.15	0.039	0.045
L3	0.25 BSC		0.100 BSC	
L4	3.80	4.10	0.150	0.161



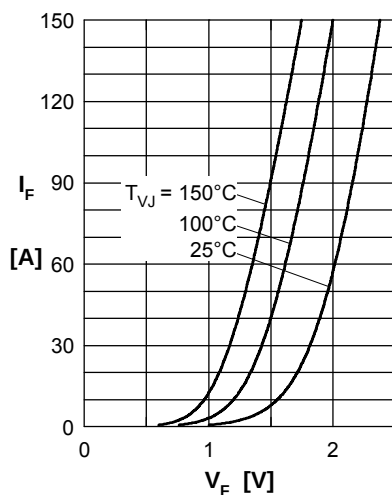
Fast Diode


Fig. 1 Forward current I_F versus V_F

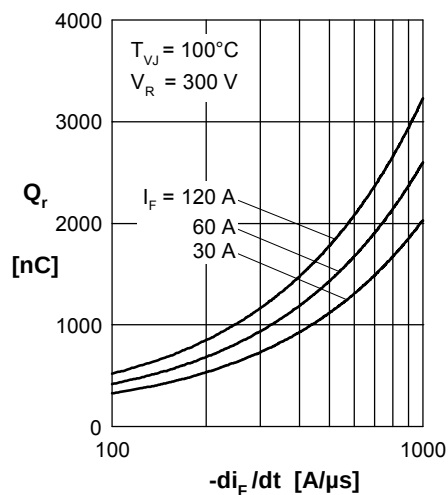


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

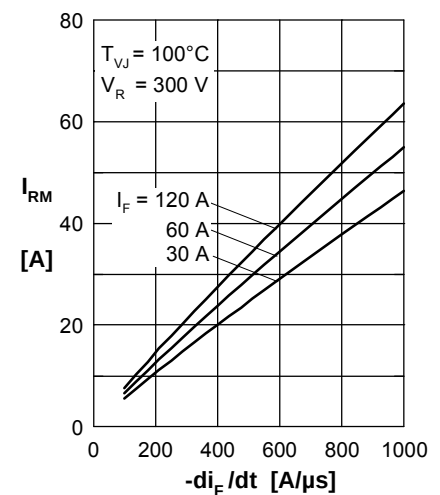


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

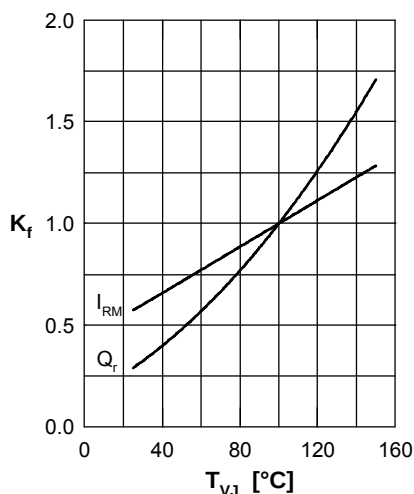


Fig. 4 Typ. dynamic parameters Q_r , I_{RM} versus T_{VJ}

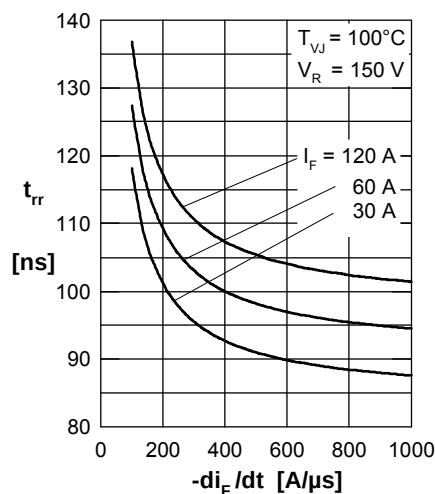


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

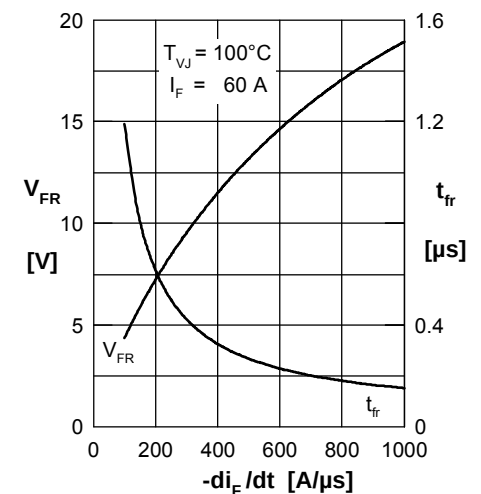


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

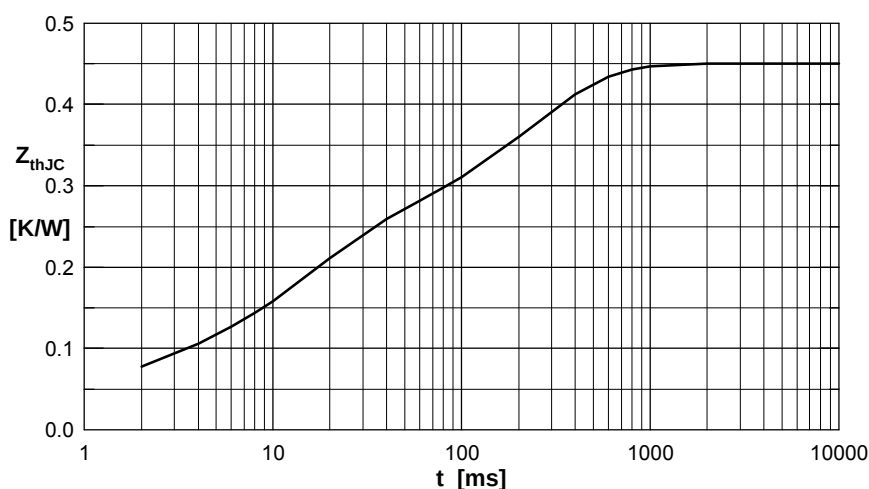


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0050	0.0001
2	0.0550	0.0010
3	0.1750	0.0140
4	0.2150	0.2300